## 2007 RCIQE International Seminar on "Advanced Semiconductor Materials and Devices"



## February 8th-9th, 2007 Conference Hall, Hokkaido University

日時: 平成19年 2月8日(木)10:00 ~ 2月9日(金)15:30

場所: 北海道大学学術交流会館

主催: 北海道大学量子集積エレクトロニクス研究センター

Research Center for Integrated Quantum Electronics (RCIQE), Hokkaido University

## **Program**

(Thursday, February 8th)		(Friday, February 9th)	
10:00 - 10:10	"Opening Address"  Takashi Fukui, Hokkaido University	- Physics and Device Application of Nanostructures -	
,		9:15-9:55	"Single-electron control of supercurrent transport in semiconductor quantum dots" Silvano De Franceschi, Jorden van Dam, Yong-Joo Doh, Leo Kouwenhoven, Aarnoud Roest and Erik Bakkers, CEA-DRFMC, Grenoble, France, Kavli Institute of Nanoscience, Delft, The Netherlands
	"Growth fundamentals of GaAs and InAs nanowires by using vapor-liquid-solid mechanism"  Kenji Hiruma, Keiichi Haraguchi, Masamitsu Yazawa and Toshio Katsuyama,		
10:50 - 11:30	Central Research Laboratory, Hitachi Ltd.  "Evolution mechanism of InAs quantum dot on	9:55-10:30	"Growth and photoluminescence study of semiconductor nanowires"  Junichi Motohisa, Hokkaido University
	GaAs(001) investigated by STMBE: in-situ STM observation during MBE growth"	10:30-10:50	Break
11:30-11:50	Shiro Tsukamoto, University of Tokyo "MOVPE growth and structural characterization of ferromagnetic MnAs nanoclusters"	10:50-11:30	"Nanoscale metal switches and their application to reconfigurable circuits" Hisao Kawaura, NEC Corporation
11:50-12:10	Shinjiro Hara, Hokkaido University  "Electrochemical formation of uniform arrays of InP nanostructures"  Taketomo Sato, Hokkaido University	11:30-12:10	"Photon-spin qubit-conversion based on dynamic nuclear polarization of a single quantum dot" Shunichi Muto, Satoru Adachi and Hirotaka Sasakura, Hokkaido University
12:10-13:30	Lunch Break	12:10-13:30	Lunch Break
- Advanced Optoelectronic and Electronic Devices -			- Carbon Nanoelectronics -
13:30-14:10	"Optical properties of GaN films for different nonpolar orientations" Holger Grahn, Paul Drude Institute, Germany	13:30-14:10	"Controlling the electronic structure of bilayer graphene"  Taisuke Ohta, Fritz Haber Institute, Germany,
14:10-14:50	"High-efficiency InAlGaN-based UV LEDs" Hideki Hirayama, RIKEN		Advanced Light Source, E. O. Lawrence Berkeley National Laboratory, USA
14:50-15:10	Break	14:10-14:50	"Electrical and optical characterization of carbon nanotube FETs"
15:10-15:50	"AlGaN/GaN HFETs for power switching applications"  Tsuyoshi Tanaka, Matsushita Electric Industrial Co., Ltd.	14:50-15:25	Takashi Mizutani, Nagoya University "Electrical properties of nano-graphite grown on silicon carbide" Kanji Yoh, Hokkaido University
15:50-16:10	"MBE growth and in-situ XPS characterization of silicon interlayers for surfaces passivation of GaAs quantum devices"  Masamichi Akazawa and Hideki Hasegawa, Hokkaido University	15:25-15:30	"Closing Remarks"  Kanji Yoh, Hokkaido University
16:10-17:40	<b>Poster Viewing Session</b>		
17:40-18:20	Lab Tour to RCIQE		
18:30-20:00	Reception (Clark Memorial Student Center 2F)		

聴講料無料、懇親会参加費 1,000円

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